

1. Description

The IRFH7440TRPBF(ES) is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product IRFH7440TRPBF(ES) is Pb-free.

2. Features

- 40V, $R_{DS(ON)}=2.2m\Omega(Typ.) @V_{GS}=10V$
- $R_{DS(ON)}=3m\Omega(Typ.) @V_{GS}=4.5V$
- High density cell design for low $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

3. Applications

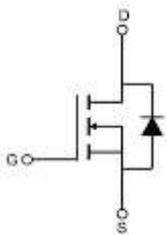
- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

100% UIS TESTED

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per Reel	Flammability Rating	Reel Size
IRFH7440TRPBF(ES)	PDFN5*6-8L	.NJ04R042/ LOT	Halogen free	Tape & Reel	5,000 PCS	UL 94V-0	13 inches

5. Pin Configuration and Functions

Pin	Function	Outline	Circuit Diagram
4	Gate	Note b 	
1/2/3	Source		
5/6/7/8	Drain		

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		BV_{DSS}	40	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	$T_C=25^{\circ}C$	I_D	93.56	A
	$T_C=100^{\circ}C$		59.17	
Maximum Power Dissipation		P_D	62.5	W
Pulsed Drain Current		I_{DM}	374.24	A
Single Pulse Avalanche Current ^a		I_{AS}	30	A
Single Pulse Avalanche Energy ^a		E_{AS}	225	mJ
Operating Junction Temperature		T_J	-55 to 150	°C
Lead Temperature		T_L	260	°C
Storage Temperature Range		T_{stg}	-55 to 150	°C

Thermal resistance ratings

Single Operation				
Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Case Thermal Resistance	$R_{\theta JC}$		2.0	°C/W

Notes:

- a. EAS condition: Starting $T_J=25^{\circ}C$, $V_{DD}=30V$, $V_G=10V$, $R_G=25\Omega$, $L=0.5mH$.
- b. This diagram is only an electrical schematic, and the actual pin size is based on POD.

Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	40			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=40V, V_{GS}=0V$			1	μA
Gate-to-source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.5	2.5	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$		2.2	4.2	m Ω
		$V_{GS}=4.5V, I_D=10A$		3	6.2	
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{ISS}	$V_{GS}=0V, f=1MHz, V_{DS}=20V$		5595		pF
Output Capacitance	C_{OSS}			411		
Reverse Transfer Capacitance	C_{RSS}			340		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS}=0 \text{ to } 10V, V_{DS}=20V, I_D=30A$		59		nC
Gate-to-Source Charge	Q_{GS}			12.5		
Gate-to-Drain Charge	Q_{GD}			15		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS}=10V, V_{DD}=20V, I_D=30A, R_G=3\Omega$		12		ns
Rise Time	t_r			16		
Turn-Off Delay Time	$t_{d(OFF)}$			39		
Fall Time	t_f			15		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=30A$			1.2	V

7. Typical Characteristics

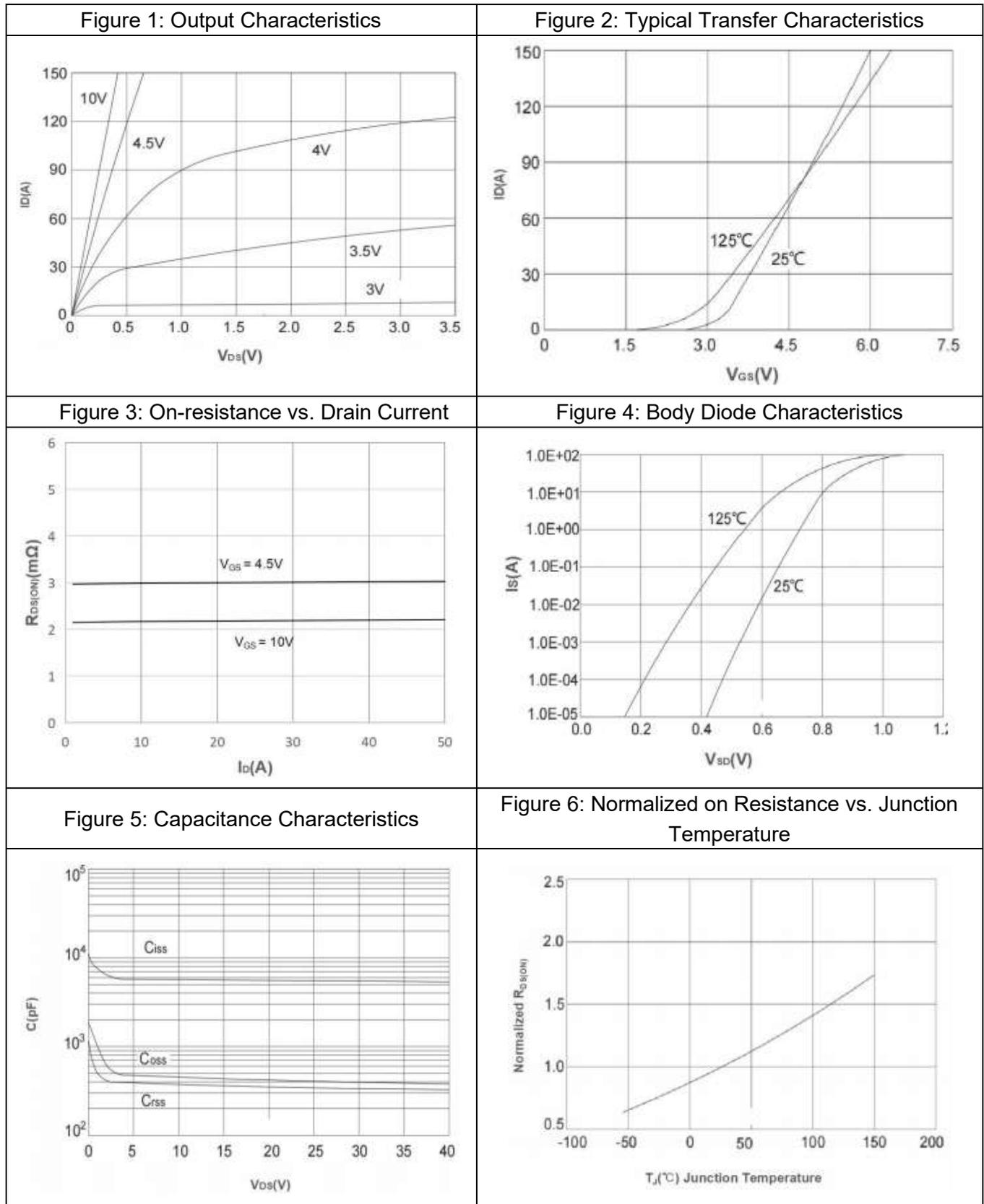
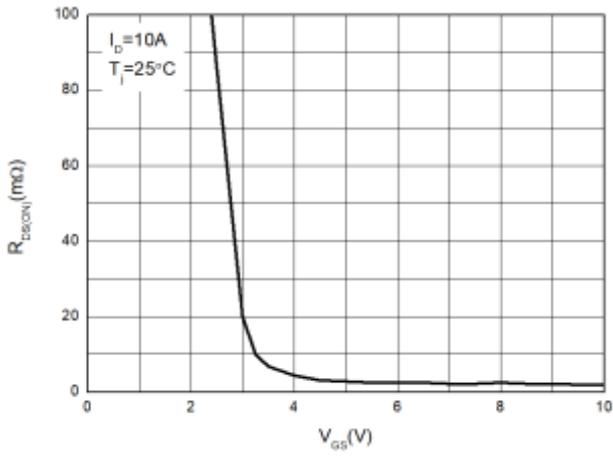


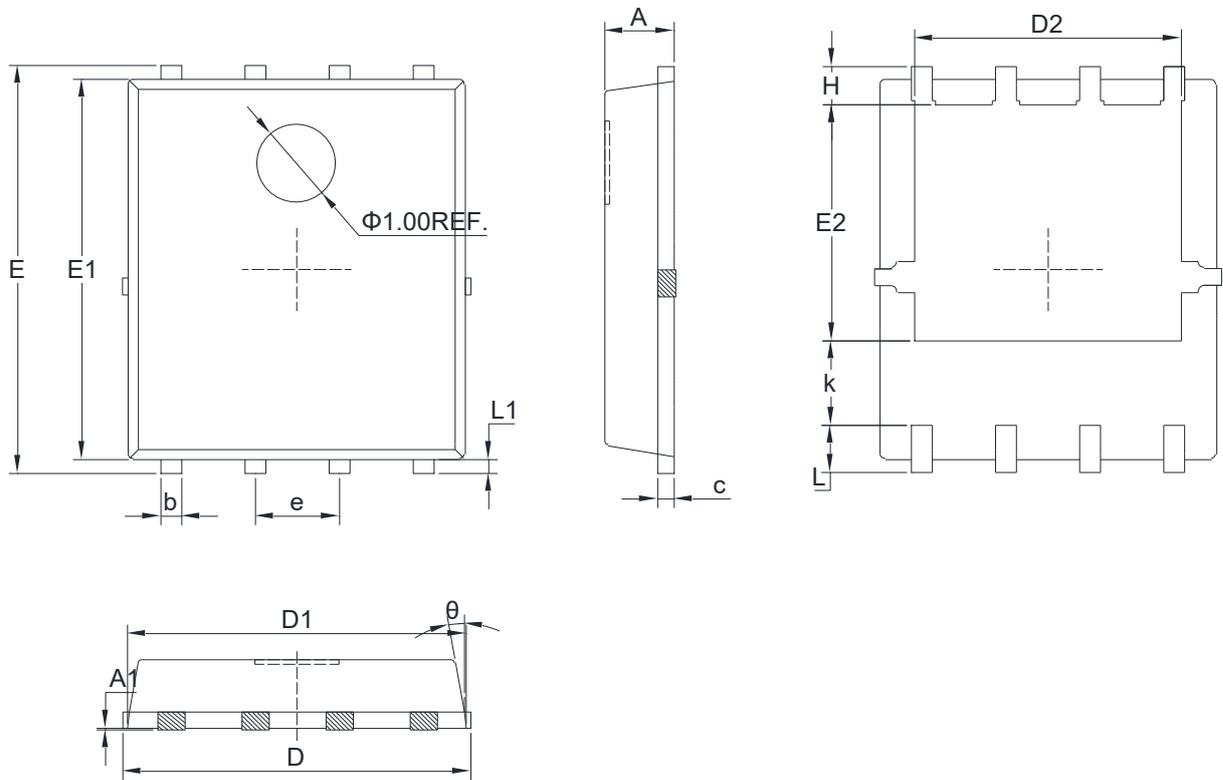


Figure7: On-resistance vs. Gate to Source



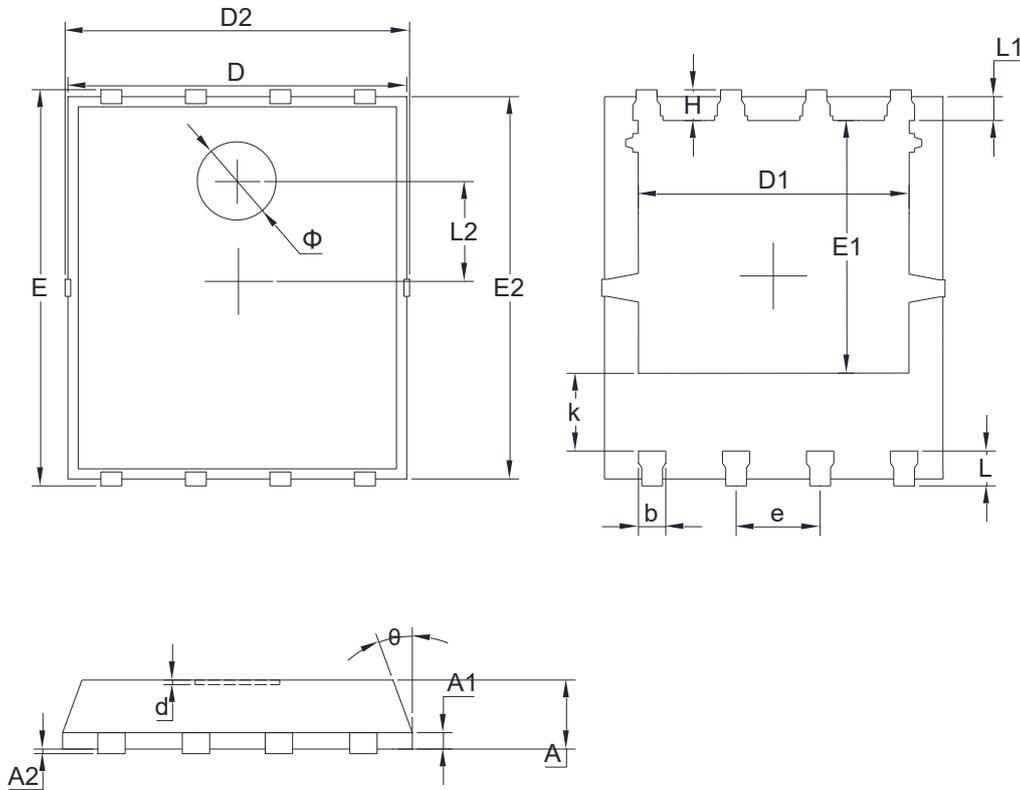
8. Dimension (PDFN5*6-8L)

POD A(Q)



Symbol	Dimensions in Millimeters			Symbol	Dimensions in Millimeters		
	MIN	NOM	MAX		MIN	NOM	MAX
A	0.90	1.00	1.10	H	0.46	0.56	0.66
A1			0.05	k	1.10		
b	0.30	0.40	0.50	L	0.51	0.61	0.71
c	0.20	0.25	0.30	L1	0.05	0.15	0.25
D	4.80	5.10	5.40	theta	8°	10°	12°
D2	3.75	3.90	4.05	D1	4.80	4.90	5.00
E	5.95	6.05	6.15				
E1	5.65	5.75	5.85				
e	1.27BCS						
E2	3.34	3.49	3.64				

POD B(X)



Symbol	Dimensions in Millimeters			Symbol	Dimensions in Millimeters		
	MIN	NOM	MAX		MIN	NOM	MAX
A	0.900	1.000	1.100	H	0.549	0.625	0.701
A1	0.254 REF			k	1.190	1.290	1.390
A2	0.000		0.050	L	0.534	0.610	0.686
D	4.824	4.900	4.976	L1	0.424	0.500	0.576
D1	3.910	4.010	4.110	θ	8°	10°	12°
D2	4.924	5.000	5.076	L2	1.800 REF		
E	5.924	6.000	6.076	Φ	1.100	1.200	1.300
E1	3.375	3.475	3.575	d			0.100
e	1.270 TYP			b	0.350	0.400	0.450
E2	5.674	5.750	5.826				

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